

PMV30UN2VL Datasheet



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DiGi Electronics Part Number PMV30UN2VL-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PMV30UN2VL

Description MOSFET N-CH 20V 5.4A TO236AB

Detailed Description N-Channel 20 V 5.4A (Ta) 490mW (Ta) Surface Mou

nt TO-236AB



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PMV30UN2VL	Nexperia USA Inc.
Series:	Product Status:
TrenchMOS™	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
20 V	5.4A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
1.2V, 4.5V	32mOhm @ 4.2A, 4.5V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
900mV @ 250μA	11 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±12V	655 pF @ 10 V
FET Feature:	Power Dissipation (Max):
	490mW (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
TO-236AB	TO-236-3, SC-59, SOT-23-3
Base Product Number:	
PMV30	

Environmental & Export classification

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



PMV30UN2

20 V, N-channel Trench MOSFET

24 April 2014

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- Enhanced power dissipation capability of 1000 mW

3. Applications

- LED driver
- Power management
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	5.4	Α
Static characte	Static characteristics						,
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 4.2 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	24	32	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



20 V, N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D
2	S	source		
3	D	drain	1 2	G—VIII
			TO-236AB (SOT23)	\$ 017aaa253

6. Ordering information

Table 3. Ordering information

Type number	Package	Package			
	Name	Description	Version		
PMV30UN2	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

7. Marking

Table 4. Marking codes

name in marking course			
Type number	Marking code		
	[1]		
PMV30UN2	%K6		

[1] % = placeholder for manufacturing site code

20 V, N-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit	
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V	
V_{GS}	gate-source voltage			-12	12	V	
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	5.4	Α	
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	4.2	Α	
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	2.7	Α	
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	18	Α	
P _{tot}	total power dissipation	T _{amb} = 25 °C	<u>[2]</u>	-	490	mW	
			[1]	-	1000	mW	
		T _{sp} = 25 °C		-	5000	mW	
Tj	junction temperature			-55	150	°C	
T _{amb}	ambient temperature			-55	150	°C	
T _{stg}	storage temperature			-65	150	°C	
Source-drain o	Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	0.9	А	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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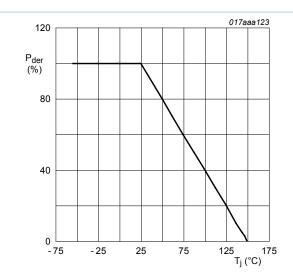


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

$$P_{\textit{der}} = \frac{P_{\textit{tot}}}{P_{\textit{tot}(25^{\circ}\textit{C})}} \times 100 \%$$

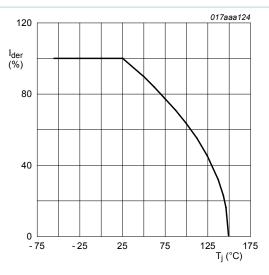
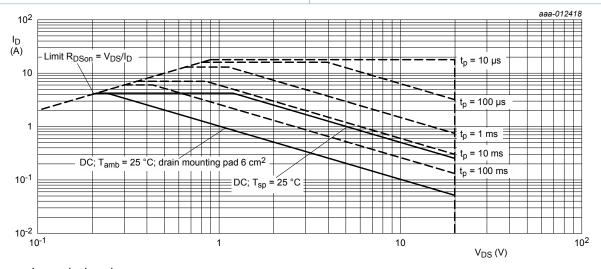


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



 I_{DM} = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	_	[1]	-	217	255	K/W
			<u>[2]</u>	-	105	124	K/W
ambient	t ≤ 5 s	<u>[2]</u>	-	73	86	K/W	

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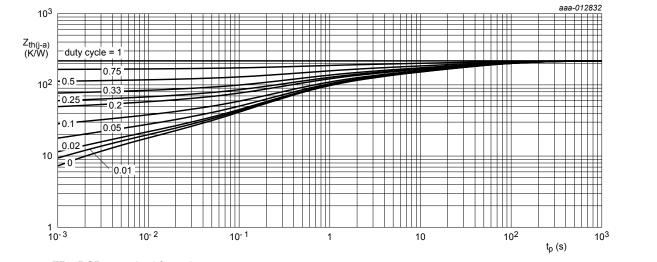
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		-	20	25	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

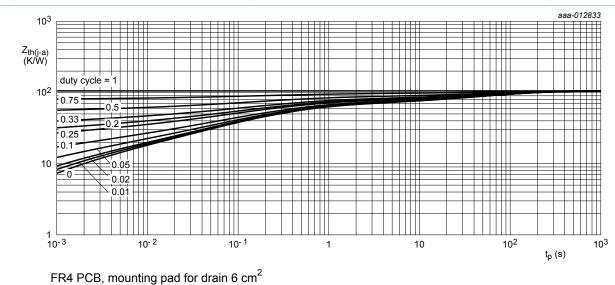


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, N-channel Trench MOSFET

10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 ^{\circ}C$	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.4	0.65	0.9	V
I _{DSS}	drain leakage current	V _{DS} = 20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V_{GS} = 4.5 V; I_D = 4.2 A; T_j = 25 °C	-	24	32	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 4.2 A; T _j = 150 °C	-	37	50	mΩ
		V_{GS} = 2.5 V; I_D = 3.7 A; T_j = 25 °C	-	30	43	mΩ
	V _{GS} = 1.8 V; I _D = 1.0 A; T _j = 25 °C	-	40	59	mΩ	
	V _{GS} = 1.5 V; I _D = 0.1 A; T _j = 25 °C	-	56	100	mΩ	
		V_{GS} = 1.2 V; I_D = 10 mA; T_j = 25 °C	-	160	-	mΩ
g _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 2 \text{ A}; T_j = 25 \text{ °C}$	-	15.8	-	S
R_G	gate resistance	f = 1 MHz; T _j = 25 °C	-	7.6	-	Ω
Dynamic ch	naracteristics				1	
Q _{G(tot)}	total gate charge	V _{DS} = 10 V; I _D = 4.2 A; V _{GS} = 4.5 V;	-	6.2	11	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.8	-	nC
Q_{GD}	gate-drain charge		-	1.4	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	655	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	70	-	pF
C _{rss}	reverse transfer capacitance		-	62	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 10 V; I _D = 4.2 A; V _{GS} = 4.5 V;	-	7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	26	-	ns
t _{d(off)}	turn-off delay time		-	35	-	ns
t _f	fall time		-	10	-	ns
Source-dra	in diode		1		-1	
V _{SD}	source-drain voltage	$I_S = 0.9 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.7	1.2	V

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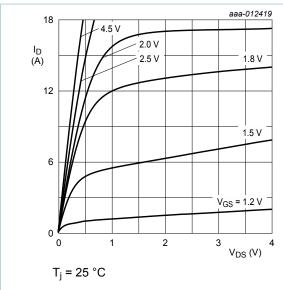


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

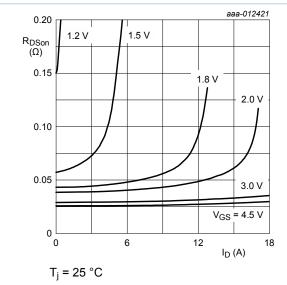


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

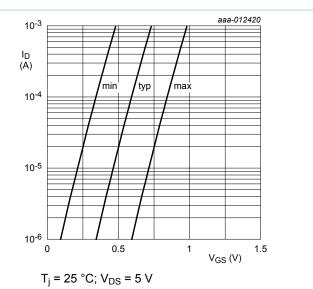


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

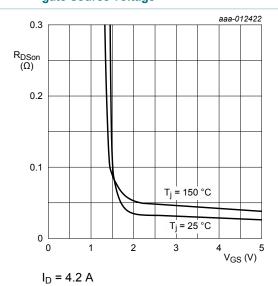


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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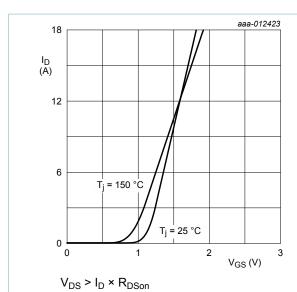


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

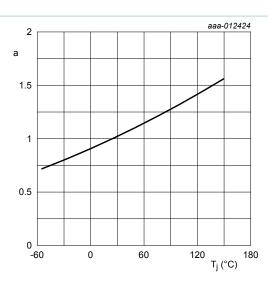


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

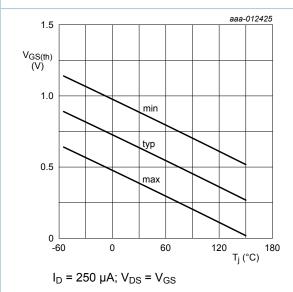


Fig. 12. Gate-source threshold voltage as a function of junction temperature

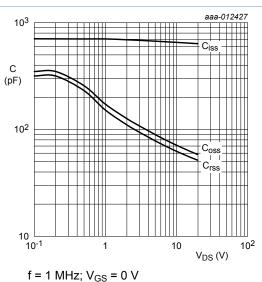


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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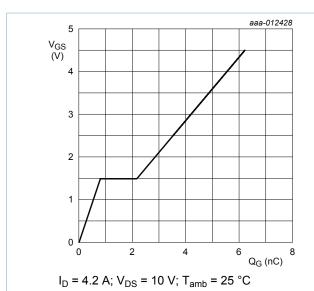


Fig. 14. Gate-source voltage as a function of gate charge; typical values

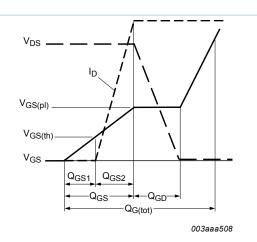


Fig. 15. MOSFET transistor: Gate charge waveform definitions

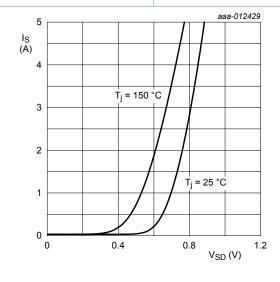
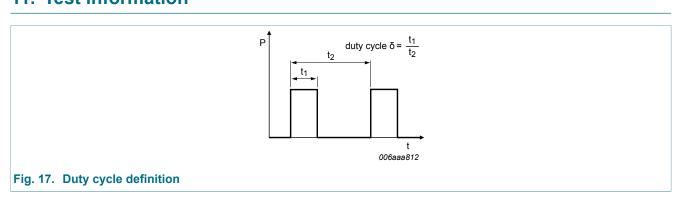


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



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12. Package outline

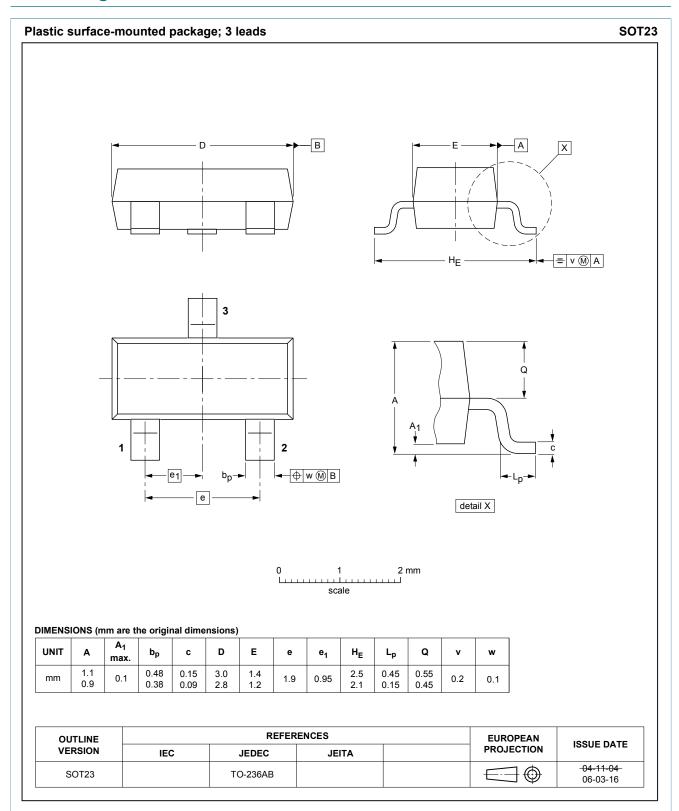
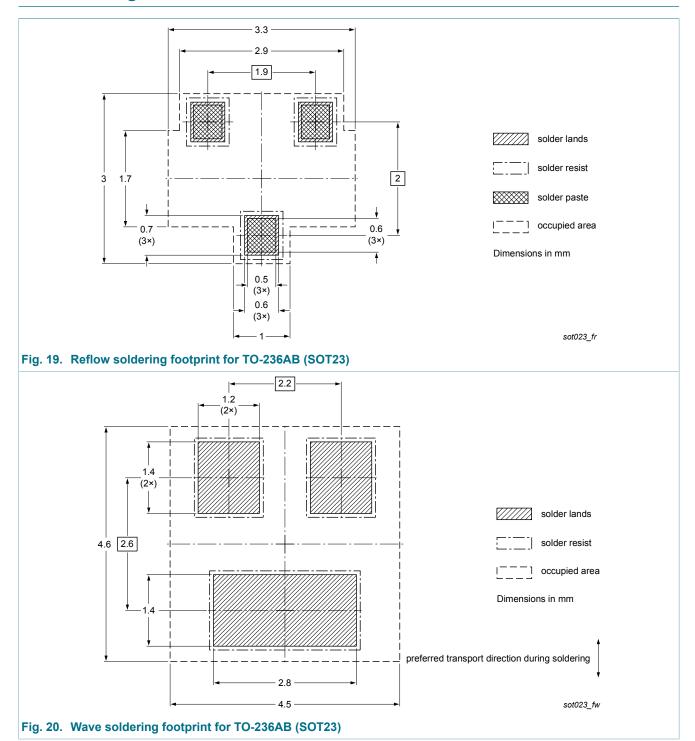


Fig. 18. Package outline TO-236AB (SOT23)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV30UN2 v.1	20140424	Product data sheet	-	-

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15. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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